

L Number	Hits	Search Text	DB	Time stamp
1	3643	((257/520) or (257/509) or (257/510) or (257/506) or (257/499) or (257/329) or (257/330) or (257/332)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 20:32
2	640	257/332	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 20:32
3	1282	257/370	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 20:32
4	5049	((((257/520) or (257/509) or (257/510) or (257/506) or (257/499) or (257/329) or (257/330) or (257/332)).CCLS.) 257/332 257/370	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 20:32
5	1	((((257/520) or (257/509) or (257/510) or (257/506) or (257/499) or (257/329) or (257/330) or (257/332)).CCLS.) 257/332 257/370) and dmos near6 power adj (element transistor device) and bipolar near2 transistor and (signal adj processing signal processor) and trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 20:33
-	9	((("4416050") or ("5476809") or ("5597742")) .PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 11:29
-	3	((("4416050") or ("5476809") or ("5597742")) .PN.	USPAT	2002/04/15 12:59
-	0	jp-63-293938\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 12:54
-	2	jp-63293938\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 12:54
-	0	ep-0292972\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 13:00
-	2	ep-292972\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 13:01
-	2	ep-429131\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 13:02
-	2	ep-566186\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 13:31
-	121	(257/499).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41
-	555	(257/506).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41
-	126	(257/509).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41

-	183	(257/520).CCLS.	USPAT; US-PGPUB	2002/04/15 13:41
-	1152	((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 18:58
-	654	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 13:54
-	341	(((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and surround\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:03
-	66	(((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 18:59
-	1	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and inductive adj load	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:06
-	1	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and (power adj transistor near12 (inductive adj load or induction or inductor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:07
-	1	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and (power adj transistor near12 (inductive adj load or induction or inductor or inductance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:09
-	3	((((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/510).CCLS.) or ((257/520).CCLS.)) and (trench or groove or sti or shallow adj trench adj isolation)) and (surround\$3 near12 transistor)) and (transistor near12 (inductive adj load or induction or inductor or inductance))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:09
-	337	(257/510).CCLS.	USPAT; US-PGPUB	2002/04/15 14:44
-	0	(257/510 and ((trench or groove) near12 (polysilicon or poly-si or polysilicon)) near12 dielectric).CCLS.	USPAT; US-PGPUB	2002/04/15 14:46
-	0	(257/510 and ((trench or groove) near12 (polysilicon or poly-si or polysilicon)) near12 (dielectric or liner or lining)).CCLS.	USPAT; US-PGPUB	2002/04/15 14:46
-	1067	((trench or groove) near12 (polysilicon or poly-si or polysilicon)) near12 (dielectric or liner or lining)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:47
-	689	((trench or groove) near6 (polysilicon or poly-si or polysilicon)) near6 (dielectric or liner or lining)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 14:53

-	37	((trench or groove) near6 (polysilicon or poly-si or polysilicon)) near6 (dielectric or liner or lining) and device adj isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 17:17
-	9	((trench or groove) near12 (device adj isolation)) same transistor) and ((polysilicon or poly-silicon or poly-si) near12 (trench or groove) near12 (lining or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 17:23
-	158	((trench or groove) near12 isolat\$3) near12 transistor) and ((polysilicon or poly-silicon or poly-si) near12 (trench or groove) near12 (lining or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:43
-	0	"n<sb>+<sb>" adj "n<sb>-<sb>" same substrate same epitaxial same trench same polysilicon same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:51
-	0	"n.sub.+" adj "n.sub.-" same substrate same epitaxial same trench same polysilicon same dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:52
-	45	erratico.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:53
-	0	("n+n-" or "p+p-") same substrate same epitaxial same (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:54
-	5	("n+n-" or "p+p-") and substrate and epitaxial and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:54
-	3	("n+n-" or "p+p-") and substrate and epitaxial and (trench or groove) and polysilicon and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 18:58
-	5	("n+n-" or "p+p-") and substrate and epitaxial and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 19:09
-	5	("n+n-" or "p+p-") and epitaxial and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 19:10
-	48	("n+n-" or "p+p-") and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/15 19:10
-	2	("6184565").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 09:22
-	1676	epitaxial same substrate same (trench or groove) same isolat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 09:24

-	1173	epitaxial same substrate same (trench or groove) same isolat\$3 and (257/\$6.ccls. or 438/\$6.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 14:26
-	3	("5998822").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 14:03
-	96	epitaxial same substrate same (trench or groove) same isolat\$3 and (257/\$6.ccls. or 438/\$6.ccls.) and power adj2 (device or transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 14:28
-	2	("5990537").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 16:49
-	2	("6184565").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/04/16 16:56
-	20	(US-6184566-\$ or US-6204112-\$ or US-5909044-\$ or US-6239465-\$ or US-6133615-\$ or US-5998822-\$ or US-5990537-\$ or US-6184565-\$ or US-5597742-\$ or US-4416050-\$ or US-5476809-\$ or US-5757081-\$ or US-6335556-\$).did. or (US-20010050388-\$ or US-20010012655-\$).did. or (EP-292972-\$ or EP-429131-\$ or EP-566186-\$).did. or (US-5243214-\$ or JP-63293938-\$).did.	USPAT; US-PGPUB; EPO; DERWENT	2002/11/12 11:36
-	12	((US-6184566-\$ or US-6204112-\$ or US-5909044-\$ or US-6239465-\$ or US-6133615-\$ or US-5998822-\$ or US-5990537-\$ or US-6184565-\$ or US-5597742-\$ or US-4416050-\$ or US-5476809-\$ or US-5757081-\$ or US-6335556-\$).did. or (US-20010050388-\$ or US-20010012655-\$).did. or (EP-292972-\$ or EP-429131-\$ or EP-566186-\$).did. or (US-5243214-\$ or JP-63293938-\$).did.) and (vertical or vmos or vmosfet or umos or umosfet)	USPAT; US-PGPUB; EPO; DERWENT; IBM_TDB	2002/11/12 08:39
-	3	(trench or sti) near6 width near6 length near6 (die or chip)	USPAT; US-PGPUB; EPO; DERWENT	2002/11/12 11:39
-	335	(257/499).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	880	(257/506).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	182	(257/509).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	251	(257/520).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40

	1581	((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/520).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:40
-	149	(((257/499).CCLS.) or ((257/506).CCLS.) or ((257/509).CCLS.) or ((257/520).CCLS.)) and trench near12 (length or width)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/12 11:41
-	23	(US-5476809-\$ or US-6184565-\$ or US-5909044-\$ or US-6204112-\$ or US-5986304-\$ or US-6288431-\$ or US-4661832-\$ or US-6184566-\$ or US-5757081-\$ or US-6335556-\$ or US-5990537-\$ or US-6239465-\$ or US-6133615-\$ or US-5998822-\$ or US-4416050-\$ or US-5597742-\$).did. or (US-20010050388-\$ or US-20010012655-\$).did. or (EP-566186-\$ or EP-429131-\$ or EP-292972-\$).did. or (JP-63293938-\$ or US-5243214-\$).did.	USPAT; US-PGPUB; EPO; DERWENT	2003/02/12 10:40
-	105	LATERAL ADJ TRENCH	USPAT; US-PGPUB; EPO; DERWENT	2003/02/12 10:55
-	97	lateral near6 (mos or mosfet or igfet or nmos or nmofset or pmos or pmofset or cmos or cmosfet or field adj effect or fet) and ((trench or groove) near12 gate near12 polysilicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:23
-	1217	((257/329) or (257/330) or (257/332)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:24
-	7	(((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate near12 separat\$3 near12 source near12 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:27
-	0	(((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate near12 (polysilicon or polycrystalline adj silicon) near12 separat\$3 near12 source near12 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 11:28
-	86	(((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) same source same drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 16:36
-	1	"6020600".PN.	USPAT	2003/02/12 16:13
-	1	"5953602".PN.	USPAT	2003/02/12 16:13
-	1	"5883399".PN.	USPAT	2003/02/12 16:14
-	1	"5773343".PN.	USPAT	2003/02/12 16:14
-	65	(((257/329) or (257/330) or (257/332)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) same source same drain and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 16:59
-	4	(((257/520) or (257/510) or (257/509) or (257/506) or (257/499)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) same source same drain and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:04
-	3	(((257/520) or (257/510) or (257/509) or (257/506) or (257/499)).CCLS.) and trench near2 gate same (polysilicon or polycrystalline adj silicon) and (dmos or dmofset).ti,ab. and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:06

-	5	((257/520) or (257/510) or (257/509) or (257/506) or (257/499)).CCLS.) and trench and (polysilicon or polycrystalline adj silicon) and (dmos or dmosfet).ti,ab. and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:07
-	93	trench and (polysilicon or polycrystalline adj silicon) and (dmos or dmosfet).ti,ab. and (epitaxial or epitaxy)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 17:55
-	2	("6124612").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:32
-	452	(257/329).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:34
-	204	((257/520) or (257/509) or (257/510) or (257/506) or (257/499) or (257/329) or (257/330) or (257/332)).CCLS.) and (epitaxy or epitaxial or epitaxially) and (lateral or laterally) near12 (mos or dmos or nmos or pmos or cmos or mosfet or nmosfet or pmosfet or cmosfet or dmosfet or field adj effect or transistor) and (trench or groove)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/12 18:57
-	2	("6239465").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:23
-	5846	cdma.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:23
-	3820	cdma.ti. and system.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:24
-	3820	cdma.ti. and system.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:25
-	435	cdma.ti. and system.ti.	USPAT	2003/02/13 13:25
-	2	("5914955").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/13 13:40
-	0	jfet adj isolation.ti. and 257/504.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 19:00
-	43	257/504.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 19:05
-	5	jfet adj isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/31 19:06

-	479	(bi-cmos or bicmos) and device near2 isolation	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 19:08
-	77	(bi-cmos or bicmos) and device near2 isolation and (latch-up latchup)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 19:59
-	0	("N.sub.+ N.sub.-" "P.sub.+ P.sub.-") and device near2 isolation and (latch-up latchup)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:00
-	0	("N.sub.+N.sub.-" "P.sub.+P.sub.-") and device near2 isolation and (latch-up latchup)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:01
-	866	257/510	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 10:19
-	1	"5316978".PN.	USPAT	2003/05/31 20:16
-	1331	shallow adj trench adj isolation.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:52
-	3	polysilicon near6 (sit shallow adj isolation adj trench) and (shallow adj trench adj isolation.ti.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:49
-	2	shallow adj trench adj isolation.ti. and polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:54
-	0	deep adj trench adj isolation.ti. and polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:54
-	0	deep adj trench adj isolation near20 polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 20:54
-	14	deep adj trench adj isolation and polysilicon adj filling	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 21:00
-	2	("6339241").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/31 21:00
-	2	("5675173").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 12:07
-	2	deep adj trench adj isolation near3 bipolar.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/06/01 12:09

-	5	deep adj trench adj isolation near6 (mos mosfet nmos nmosfet pmos pmosfet bipolar).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 12:10
-	90	deep adj trench adj isolation.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:45
-	8	deep adj trench adj isolation and cmos and power.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:47
-	0	deep adj trench adj isolation near20 power adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:48
-	12	deep adj trench adj isolation and power adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 13:48
-	0	deep adj trench adj isolation and power adj transistor and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 14:49
-	300	power adj (device transistor) near20 (cmos cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 14:51
-	117	power adj (device transistor) near3 (cmos cmosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 14:51
-	35	power adj (device transistor) near3 (cmos cmosfet).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 15:01
-	1	power adj (device transistor) near3 (cmos cmosfet).ti,ab,clm. and (latch-up or latchup)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/06/01 15:02
-	4	899573.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/15 18:40
-	38	bcd adj technology	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/15 18:40
-	2	bcd adj technology and signal adj processing	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/15 18:47
-	2	("4631803").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/15 18:48

-	53	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos) and (latch-up latch adj "up" latch adj "up")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 18:52
-	15	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos) and (latch-up latch adj "up" latch adj "up") and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:03
-	2394	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:05
-	28	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm. and substrate.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:04
-	21	((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm. and substrate.clm.) not ((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos) and (latch-up latch adj "up" latch adj "up") and substrate)) and bcd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:04
-	27	((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm. and substrate.clm.) not ((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos) and (latch-up latch adj "up" latch adj "up") and substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:04
-	27	((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm. and substrate.clm.) not ((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos) and (latch-up latch adj "up" latch adj "up") and substrate)) and (bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:15
-	27	((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos).ti,ab,clm. and substrate.clm.) not ((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos) and (latch-up latch adj "up" latch adj "up") and substrate)) and (bcd bipolar-cmos-dmos bipolar adj cmos adj dmos bicmos).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:15
-	5307	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos bicmos).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:15
-	432	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos bicmos).ti,ab,clm. and substrate.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:15
-	216	(bcd bipolar-cmos-dmos bipolar adj cmos adj dmos bicmos).ti,ab,clm. and substrate.clm. and (isolating isolation insulating insulator).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:28
-	2	("6351021").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:34
-	276	((bcd bipolar-cmos-dmos bipolar adj cmos adj dmos bicmos).ti,ab,clm. and substrate.clm. and (isolating isolation insulating insulator).clm.) LL8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/15 19:35

-	77	trench adj isolation and (dmos bcd bipolar-cmos-dmos) and (N+ P+)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 16:37
-	0	trench adj isolation and (bcd bipolar-cmos-dmos) and (dmos dmosfet) and (N+ P+)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 16:38
-	0	trench adj isolation and bipolar-cmos-dmos and (dmos dmosfet) and (N+ P+)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 16:38
-	0	trench adj isolation and bipolar-cmos-dmos and (N+ P+)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 16:38
-	1	trench near6 (isolating isolation insulating insulation) and bipolar-cmos-dmos and (N+ P+)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 17:05
-	0	ep-00830492\$--.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 18:20
-	9	erratico.in.	EPO	2004/02/16 18:38
-	2	("6175277").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 18:50
-	0	("dmos.ti.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 18:50
-	559	dmos.ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 19:15
-	5	cmos near6 signal adj processing and bipolar near6 (power high-voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 19:17
-	1	cmos near6 signal adj processing and bipolar near6 (power high-voltage) and bipolar and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/16 19:17